

Description

The IRFR3806TRPBF uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

V_{DS} = 60V I_D =50 A

 $R_{DS(ON)} < 15m\Omega @ V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply

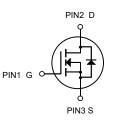
Package Marking and Ordering Information

ſ	Product ID	Pack	Marking	Qty(PCS)
ſ	IRFR3806TRPBF	TO-252-2L(TO-252-2(DPAK))	RFR3806 XXXX	2500

Absolute Maximum Ratings (Tc=25°Cunless otherwise noted)

Symbol	Parameter	Rating	Units	
VDS	Drain-Source Voltage	60	V	
Vgs	Gate-Source Voltage	±20	V	
I₀@Tc=25°C	Continuous Drain Current, V _{GS} @ 10V ¹	50	А	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	Pulsed Drain Current ² 90		
Ідм	Pulsed Drain Current ²			
EAS	Single Pulse Avalanche Energy ³			
las	Avalanche Current	28	А	
P _D @T _C =25°C	Total Power Dissipation ⁴	45	W	
P _D @T _A =25°C	Total Power Dissipation ⁴	2	W	
Тѕтс	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
Reja	Thermal Resistance Junction-Ambient ¹	62	°C/W	
Rejc	ReJC Thermal Resistance Junction-Case ¹		°C/W	





N-Channel MOSFET



IRFR3806TRPBF

N-Channel Enhancement Mode MOSFET

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	60			V
∆BVbss/∆Tj	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =1mA		0.057		V/°C
		V _{GS} =10V , I _D =20A		11	15	
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =4.5V , I _D =10A		15	20	mΩ
VGS(th)	Gate Threshold Voltage		1.2		2.5	V
$\bigtriangleup V_{\text{GS(th)}}$	V _{GS(th)} Temperature Coefficient	V _{GS} =V _{DS} , I _D =250uA		-5.68		mV/°C
		V _{DS} =48V , V _{GS} =0V , T _J =25°C			1	
IDSS	Drain-Source Leakage Current	V _{DS} =48V , V _{GS} =0V , T _J =55°C			5	uA
lgss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =15A		45		S
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		1.7		Ω
Qg	Total Gate Charge (4.5V)			19.3		
Qgs	Gate-Source Charge			7.1		nC
Q _{gd}	Gate-Drain Charge	_		7.6		
Td(on)	Turn-On Delay Time			7.2		
Tr	Rise Time	V _{DD} =30V , V _{GS} =10V ,		50		
Td(off)	Turn-Off Delay Time	R _G =3.3 ,		36.4		ns
T _f	Fall Time	I _D =15A		7.6		
Ciss	Input Capacitance			2423		
Coss Output Capacitance VDS=15				145		pF
Crss	Reverse Transfer Capacitance	_		97		
ls	Continuous Source Current ^{1,5}				35	А
lsм	Pulsed Source Current ^{2,5}	$-V_G=V_D=0V$, Force Current			80	А
Vsd	Diode Forward Voltage ²	V _{GS} =0V , I _S =A , T _J =25°C			1	V
trr	Reverse Recovery Time			16.3		nS
Qrr	Reverse Recovery Charge	IF=15A , dI/dt=100A/μs , Tյ=25℃		11		nC

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Note :

1. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.

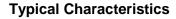
2.The data tested by pulsed , pulse width \leqq 300us , duty cycle \leqq 2%

3. The EAS data shows Max. rating . The test condition is VDD=25V, VGS=10V, L=0.1mH, IAS=28A

4. The power dissipation is limited by 150° junction temperature 5. The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation



IRFR3806TRPBF N-Channel Enhancement Mode MOSFET



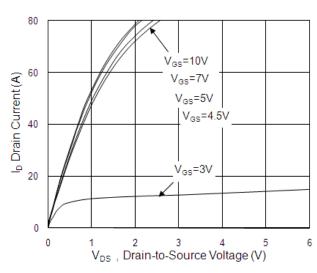


Fig.1 Typical Output Characteristics

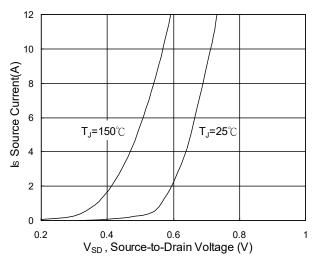


Fig.3 Forward Characteristics of Reverse

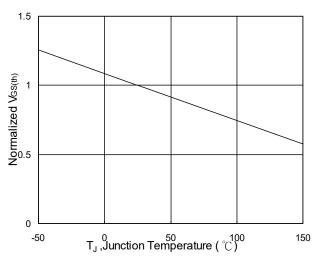


Fig.5 Normalized $V_{GS(th)}\,v.s\;T_J$

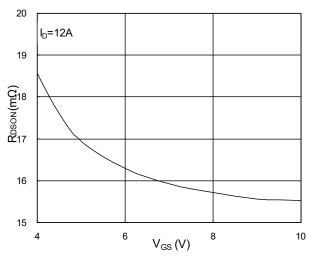


Fig.2 On-Resistance v.s Gate-Source

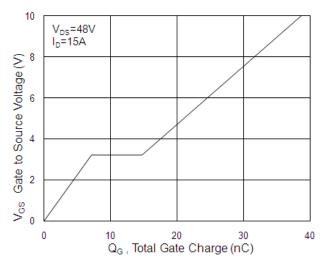


Fig.4 Gate-Charge Characteristics

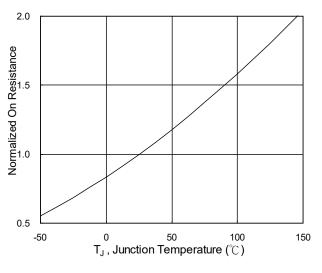
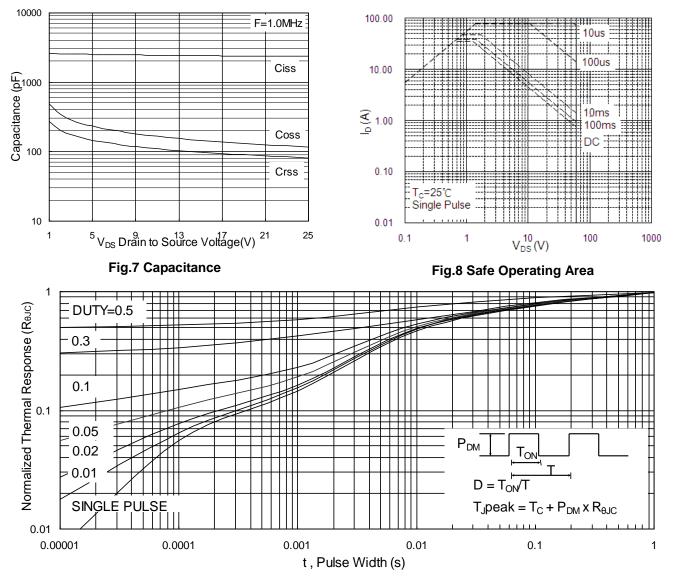
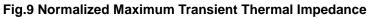


Fig.6 Normalized R_{DSON} v.s T_J







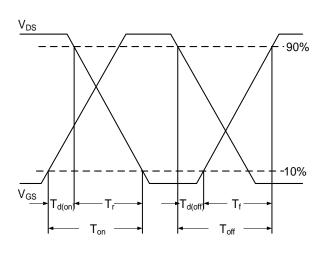


Fig.10 Switching Time Waveform

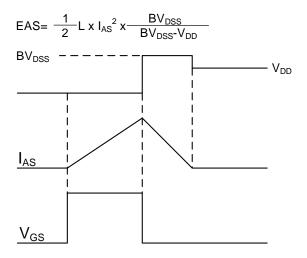
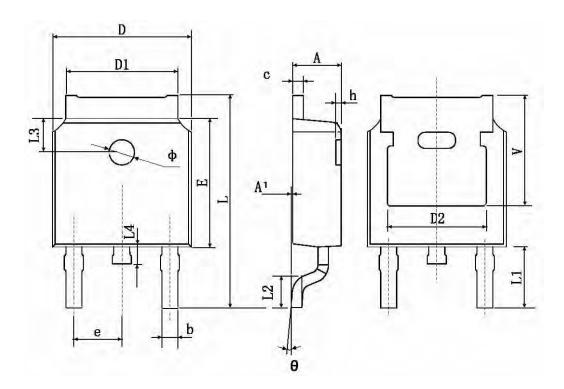


Fig.11 Unclamped Inductive Switching Waveform



TO-252-2L(TO-252-2(DPAK)) Package Information



Ormhal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
с	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483	TYP.	0.190	TYP.	
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	TYP.	0.211 TYP.		



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